

N-Channel Enhancement Mode Power MOSFET

Description

The HM3207T uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in Automotive applications and a wide variety of other applications.

General Features

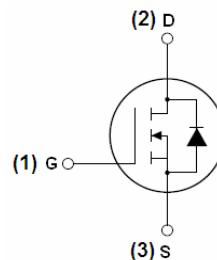
- $V_{DSS} = 75V, I_D = 210A$
 $R_{DS(ON)} < 4m\Omega @ V_{GS} = 10V$
- Good stability and uniformity with high E_{AS}
- Special process technology for high ESD capability
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

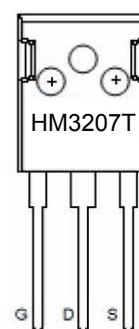
- Automotive applications
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

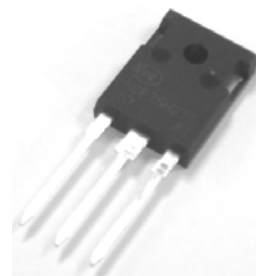
100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin assignment



TO-247 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM3207T	HM3207T	TO-247	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DSS}	75	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	210	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	150	A
Pulsed Drain Current	I_{DM}	840	A
Maximum Power Dissipation	P_D	330	W
Derating factor		2.2	W/ $^\circ C$
Single pulse avalanche energy ^(Note 4)	E_{AS}	2200	mJ

Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C
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Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 1)	$R_{\theta JC}$	0.455	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

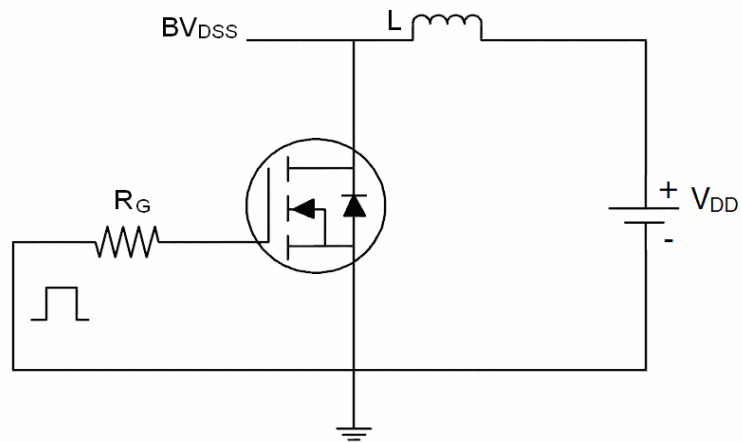
Parameter	Symbol	Condition	Min	Typ	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	75			V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=75V, V_{GS}=0V$			1	μA	
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 200	nA	
On Characteristics							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=40A$		25°C	2.9	4	m Ω
				125°C	4.7	6.5	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=40A$	100	165		S	
Dynamic Characteristics							
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0MHz$		11000		PF	
Output Capacitance	C_{oss}			914		PF	
Reverse Transfer Capacitance	C_{rss}			695		PF	
Switching Characteristics							
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=2A, R_L=15\Omega$ $V_{GS}=10V, R_G=2.5\Omega$		23		nS	
Turn-on Rise Time	t_r			190		nS	
Turn-Off Delay Time	$t_{d(off)}$			130		nS	
Turn-Off Fall Time	t_f			120		nS	
Total Gate Charge	Q_g	$I_D=30A, V_{DD}=30V, V_{GS}=10V$	-	250		nC	
Gate-Source Charge	Q_{gs}			48		nC	
Gate-Drain Charge	Q_{gd}			98		nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=40A$			1.2	V	
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = 40A$ $di/dt = 100A/\mu s^{(Note2)}$		48		nS	
Reverse Recovery Charge	Q_{rr}			78		nC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)					

Notes:

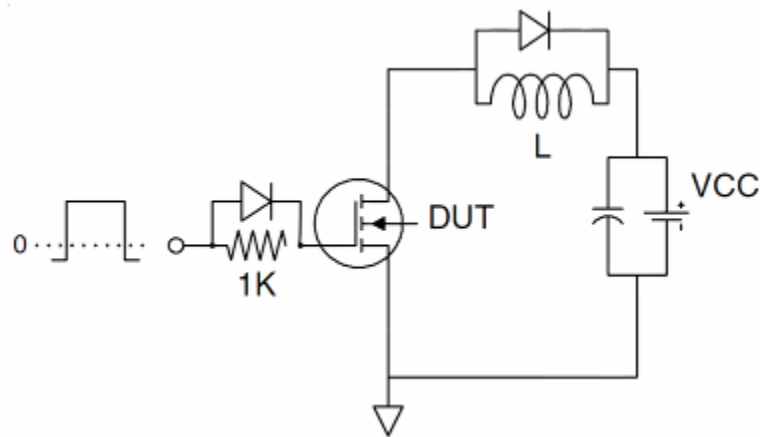
- Surface Mounted on FR4 Board, $t \leq 10$ sec.
- Pulse Test: Pulse Width $\leq 400\mu s$, Duty Cycle $\leq 2\%$.
- EAS condition: $T_J=25^\circ C, V_{DD}=37.5V, V_G=10V, L=0.5mH, R_G=25\Omega, I_{AS}=37A$

Test circuit

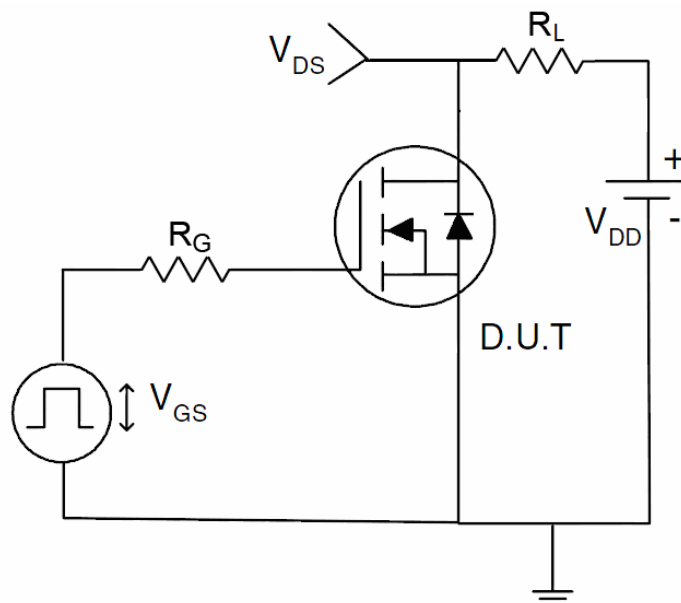
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

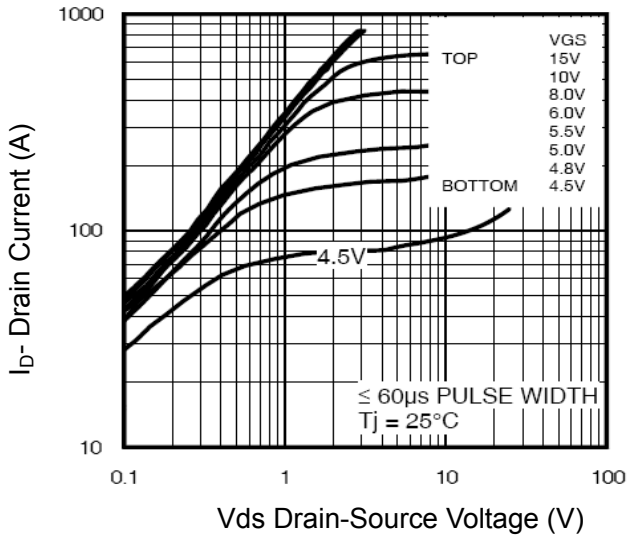


Figure 1 Output Characteristics

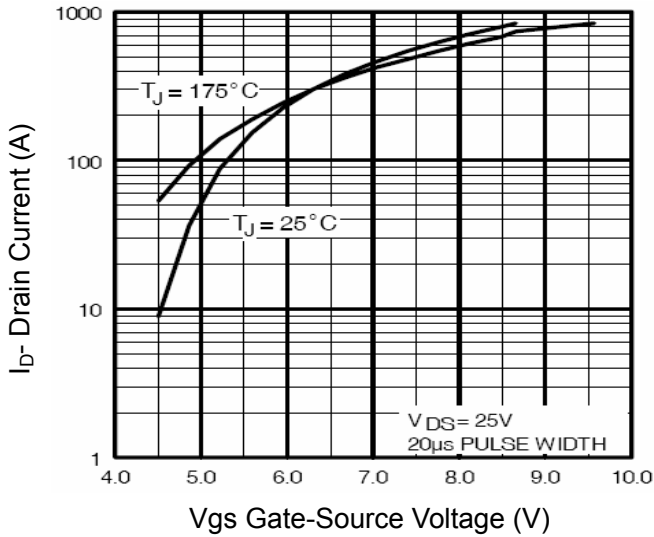


Figure 2 Transfer Characteristics

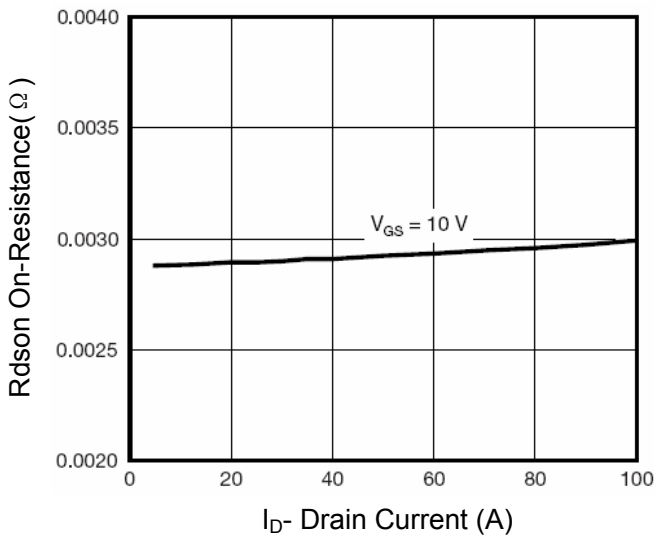


Figure 3 $R_{DS(on)}$ - Drain Current

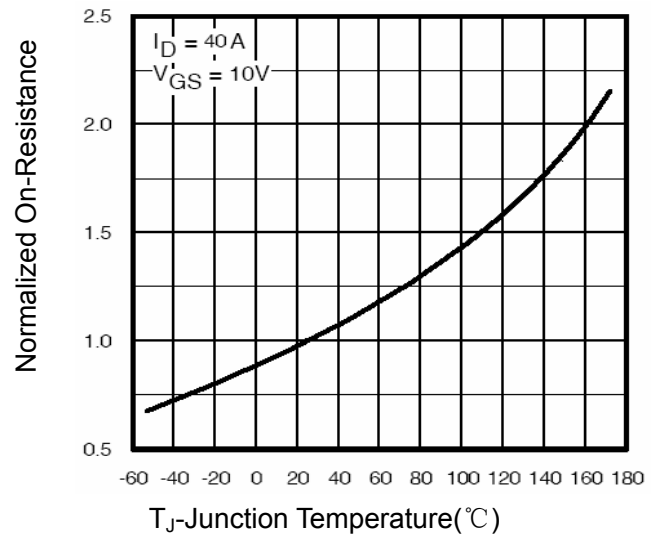


Figure 4 $R_{DS(on)}$ -Junction Temperature

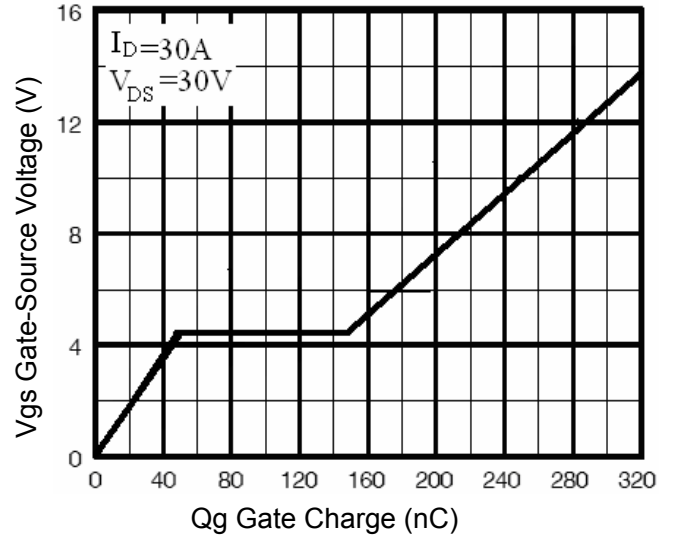


Figure 5 Gate Charge

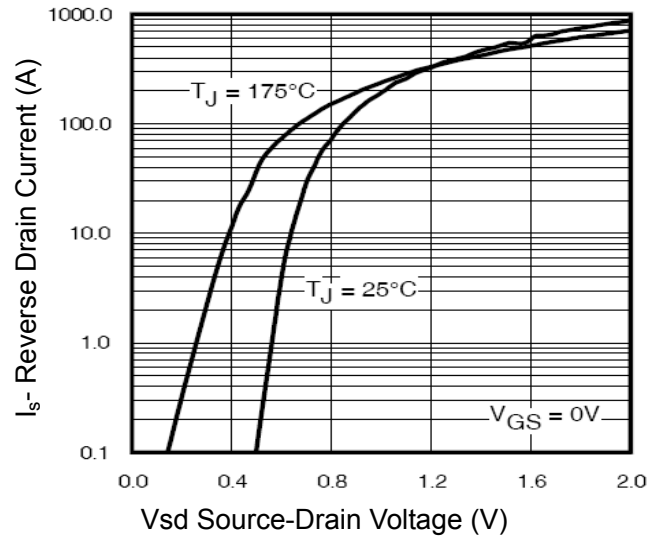


Figure 6 Source- Drain Diode Forward

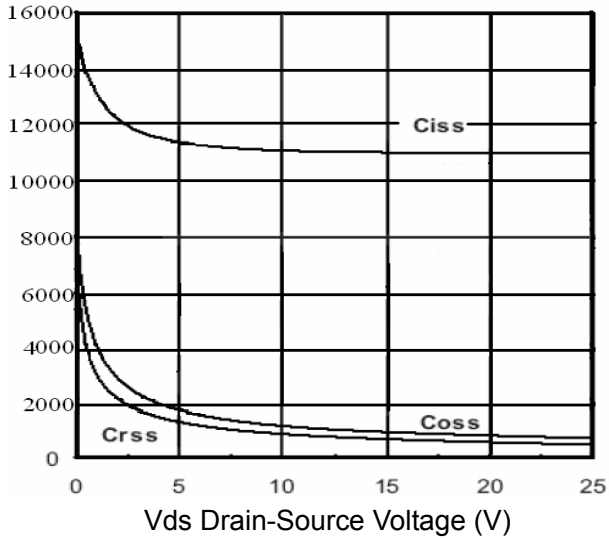


Figure 7 Capacitance vs Vds

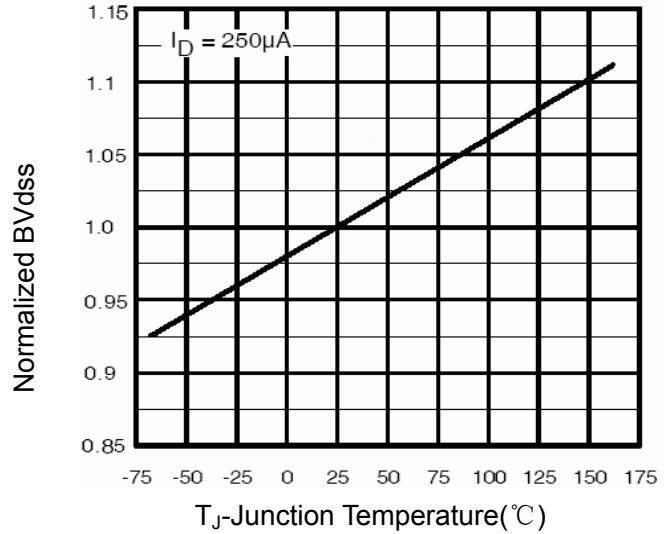


Figure 9 BV_{DSS} vs Junction Temperature

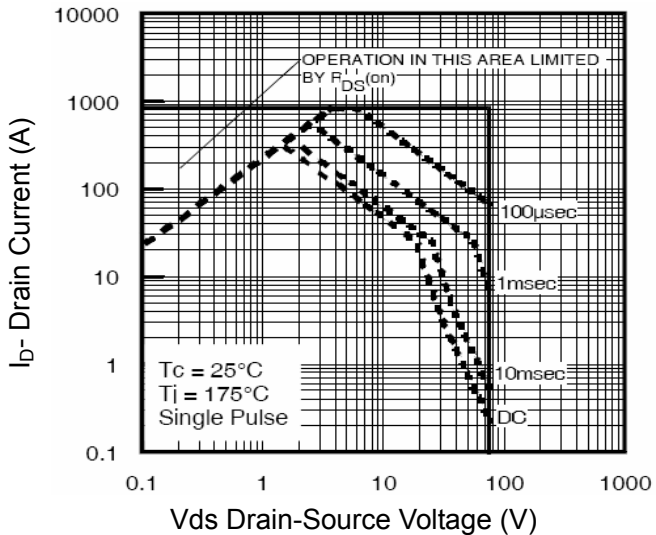


Figure 8 Safe Operation Area

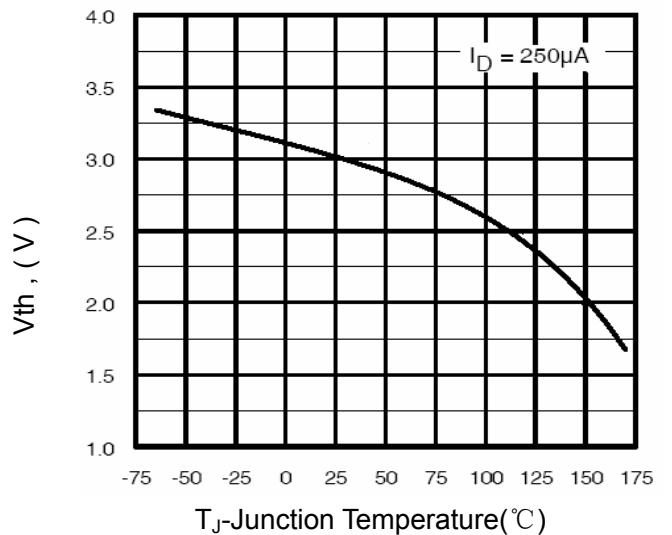


Figure 10 $V_{GS(th)}$ vs Junction Temperature

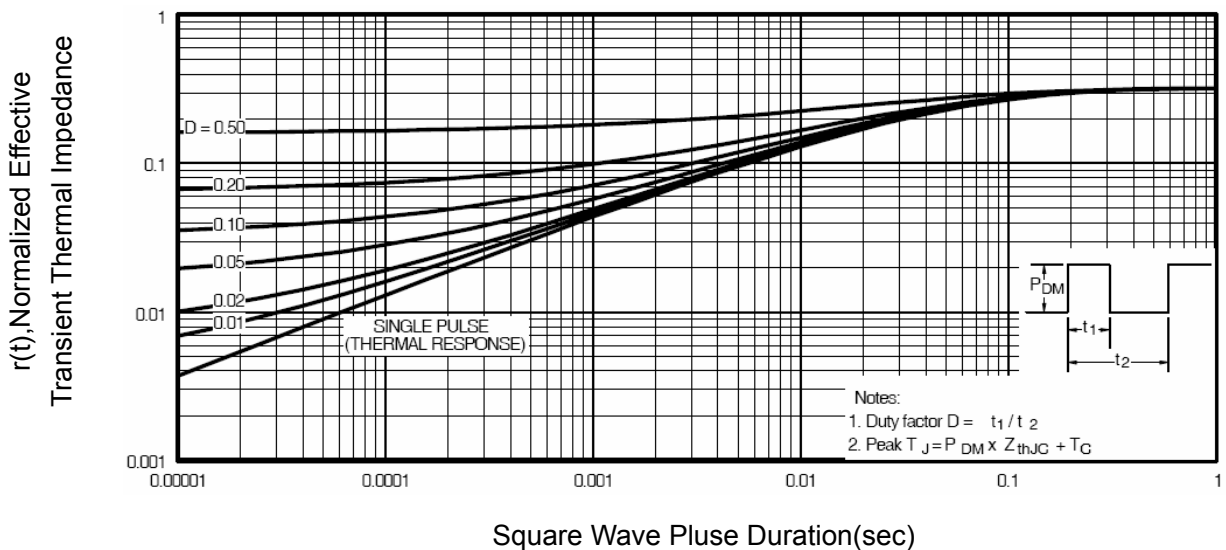
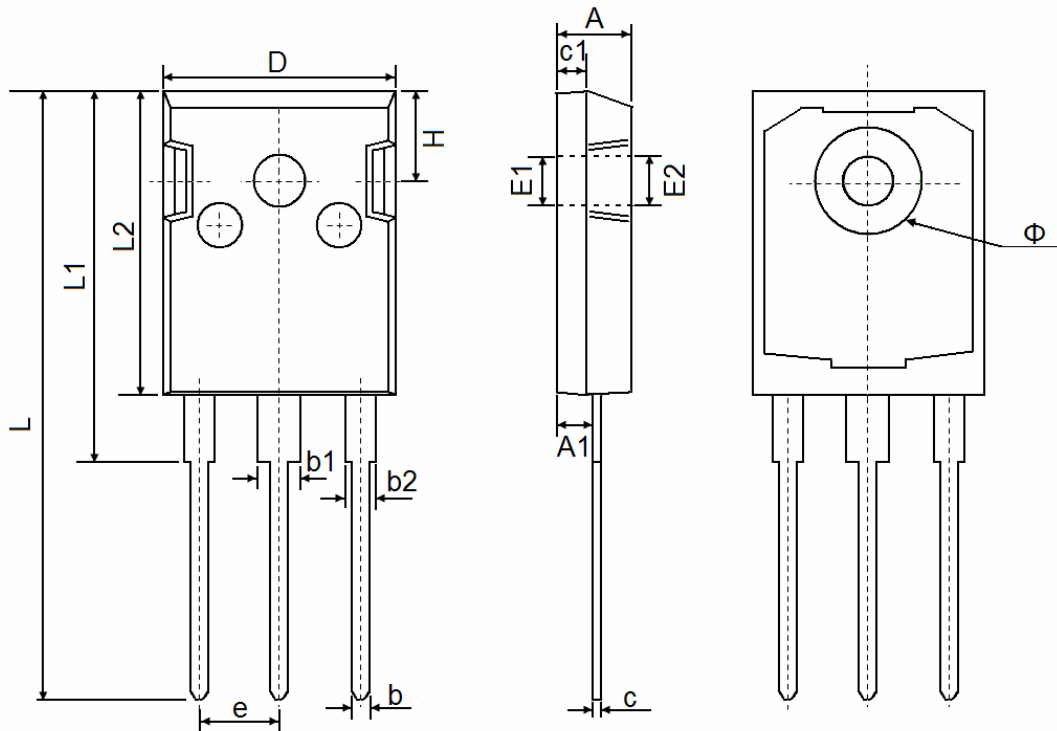


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-247 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	